

RHOS

### SOT-23



1. BASE

2. EMITTER

3. COLLECTOR

#### MARKING: 2A

### Features

• As complementary type the NPN transistor S9014 is recommended

Epitaxial planar die construction

### **Maximum Ratings**

(Ratings at 25°C ambient temperature unless otherwise specified.)

Symbol	Parameter	Value	Units
V <sub>сво</sub>	Collector-Base Voltage	-50	V
VCEO	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-100	mA
Pc	Total Device Dissipation	200	mW
R <sub>0JA</sub>	Thermal Resistance Junction to Ambient	625	°C/W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55 to +150	°C

## **Electrical Characteristics**

(Ratings at  $25^{\circ}$ C ambient temperature unless otherwise specified).

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V <sub>CBO</sub>	Ι <sub>C</sub> =-10μΑ, Ι <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-45		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> =-10μΑ, I <sub>C</sub> =0	-5	1	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0		-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-0.1	μA
DC current gain	h <sub>FE(2)</sub>	<sub>2)</sub> V <sub>CE</sub> =-5V, I <sub>C</sub> = -1mA		1000	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> = -10mA		-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> = -10mA		-1	V
Transition frequency		$V_{CE}$ =-5V, I <sub>C</sub> =-10mA,f=30MHz	150		MHz

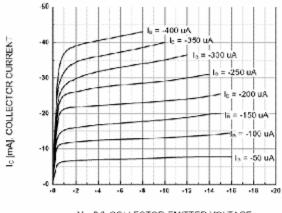
#### CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	L	Н
Range	200-450	450-1000



### SOT-23 Plastic-Encapsulate Transistors(PNP)





V<sub>CE</sub> [V], COLLECTOR-EMITTER VOLTAGE



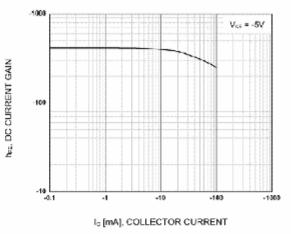


Figure 2. DC current Gain

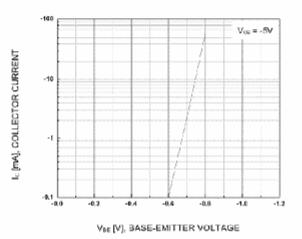
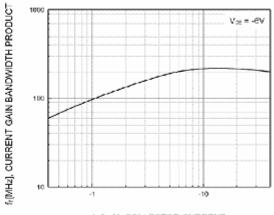


Figure 4. Base-Emitter On Voltage

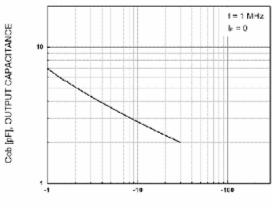


Ic [mA], COLLECTOR CURRENT



Ic [mA], COLLECTOR CURRENT

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage



Vc8 [V], COLLECTOR-BASE VOLTAGE

Figure 5. Collector Output Capacitance

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